



SPN4842

N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN4842 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high-side switching .

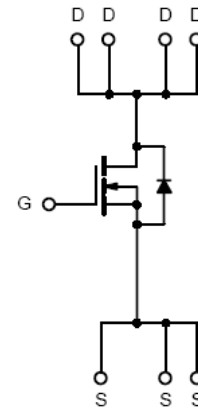
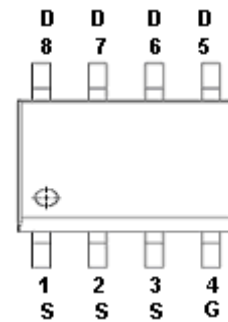
FEATURES

- ◆ 45V/6A, $R_{DS(ON)}=8m\Omega@V_{GS}=10V$
- ◆ 45V/3A, $R_{DS(ON)}=12m\Omega@V_{GS}=4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

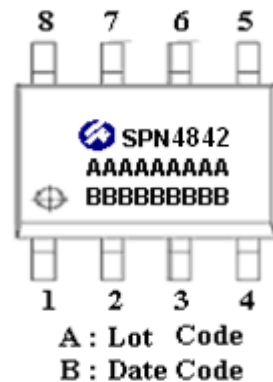
APPLICATIONS

- DC/DC Converter
- Load Switch
- Synchronous Buck Converter
- Charger Adapter
- LED Lighting

PIN CONFIGURATION(SOP – 8P)



PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN4842S8RGB	SOP-8P	SPN4842

※ SPN4842S8RGB : 13" Tape Reel ; Pb – Free ; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V _{DSS}	45	V	
Gate –Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current	I _D	TA=25°C	13.3	A
		TA=100°C	8.4	
Pulsed Drain Current	I _{DM}	53.2	A	
Single Pulse Avalanche Energy	E _{AS}	38	mJ	
Avalanche Current	I _{AS}	27	A	
Power Dissipation	P _D	TA=25°C	2.5	W
		TA=70°C	1.4	
Operating Junction Temperature	T _J	-55/150	°C	
Storage Temperature Range	T _{STG}	-55/150	°C	
Thermal Resistance-Junction to Ambient	R _{θJA}	50	°C/W	



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ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	45			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.5	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=45V, V_{GS}=0V, T_J=25^\circ C$			1	μA
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=6A$		6	8	m Ω
		$V_{GS}=4.5V, I_D=3A$		8	12	
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=6A$		25		S
Diode Forward Voltage	V_{SD}	$I_S=13.3A, V_{GS}=0V$			1.5	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=20V, V_{GS}=10V$ $I_D=13.3A$		31.5		nC
Gate-Source Charge	Q_{gs}			3.5		
Gate-Drain Charge	Q_{gd}			9		
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V$ $f=1MHz$		1600		pF
Output Capacitance	C_{oss}			180		
Reverse Transfer Capacitance	C_{rss}			130		
Turn-On Time	$t_{d(on)}$	$V_{DD}=20V,$ $I_D=13.3A, V_{GS}=10V$ $R_G=6\Omega$		12		nS
	t_r			82		
Turn-Off Time	$t_{d(off)}$			33		
	t_f			59		
Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1MHz$		1.2		Ω

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=27A, R_G=25\Omega, \text{Starting } T_J=25^\circ C$
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.



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TYPICAL CHARACTERISTICS

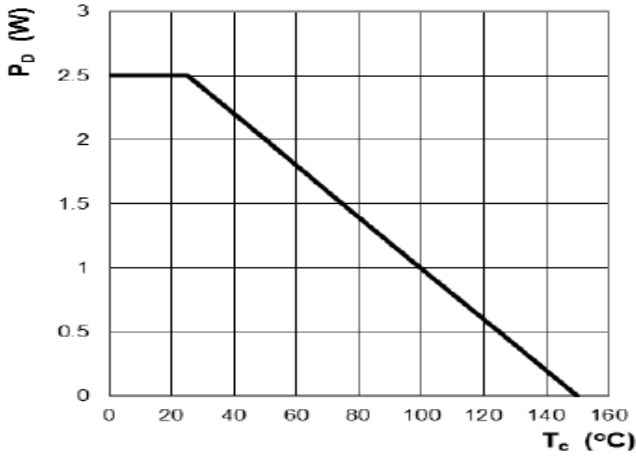


Figure 1: Power Dissipation

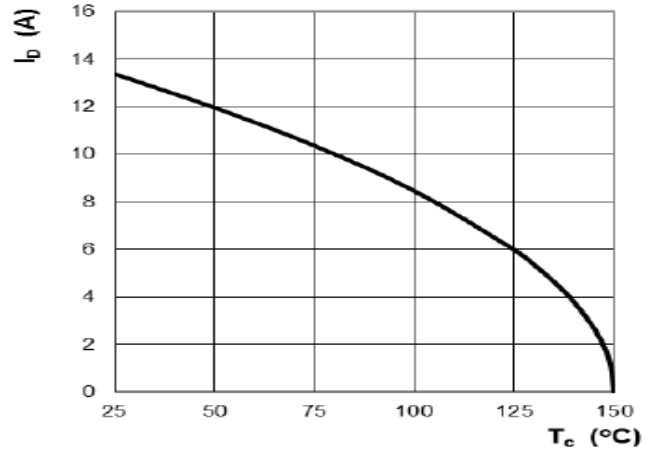


Figure 2: Continuous Drain Current vs. T_c

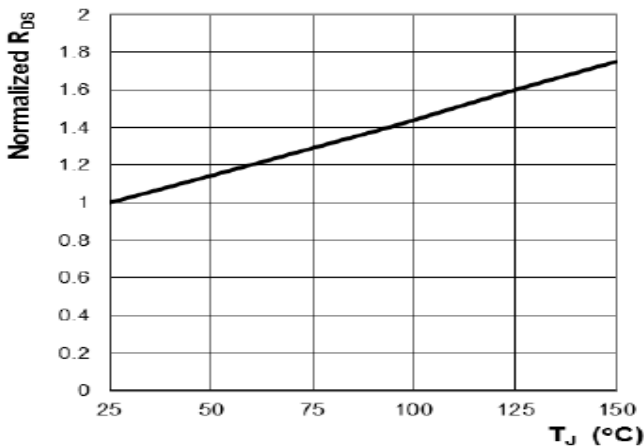


Figure 3: Normalized $R_{DS(on)}$ vs. T_J

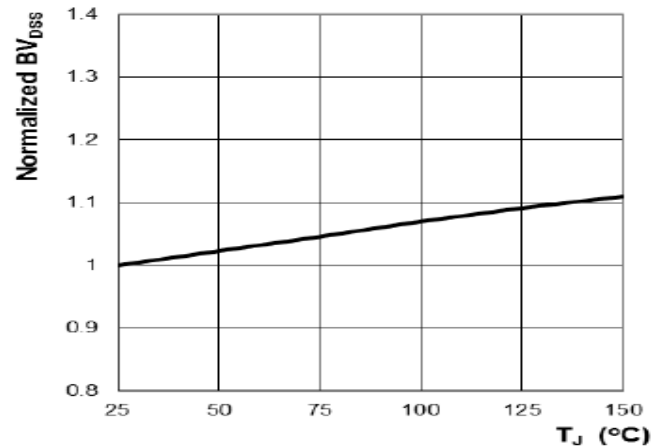


Figure 4: Normalized BV_{DSS} vs. T_J

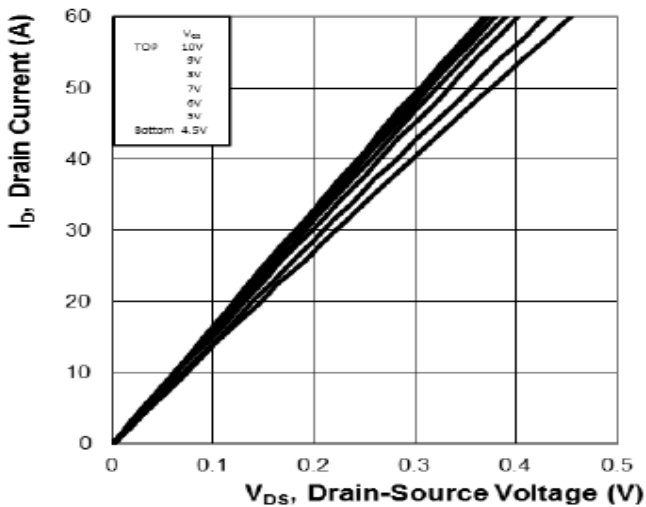


Figure 5: On-Region Characteristics

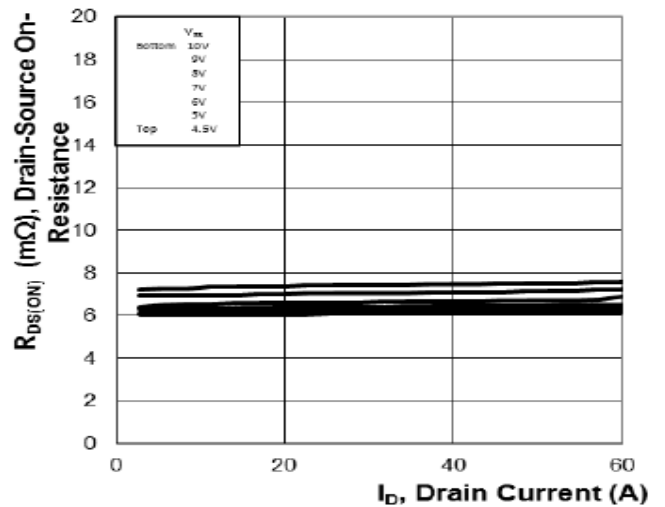


Figure 6: Typ. R_{DS} Variation vs. I_D and V_{GS}



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TYPICAL CHARACTERISTICS

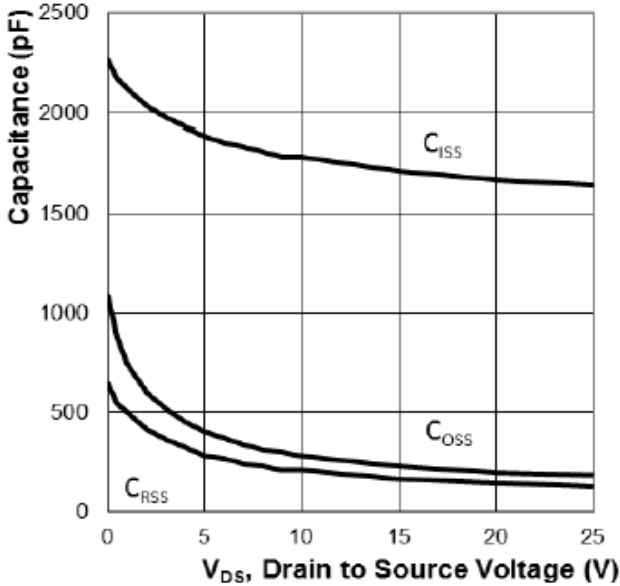


Figure 7: Typ. Capacitance Characteristics

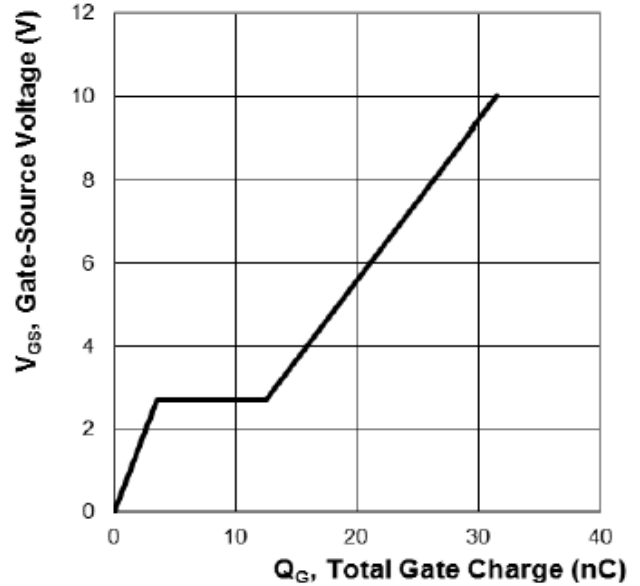


Figure 8: Typ. Gate Charge Characteristics

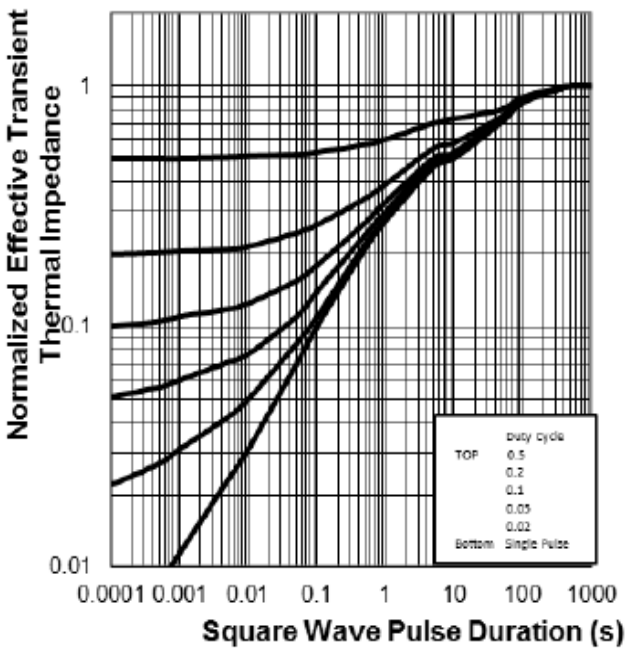


Figure 9: Normalized Thermal Transient Impedance, Junction-to-Case

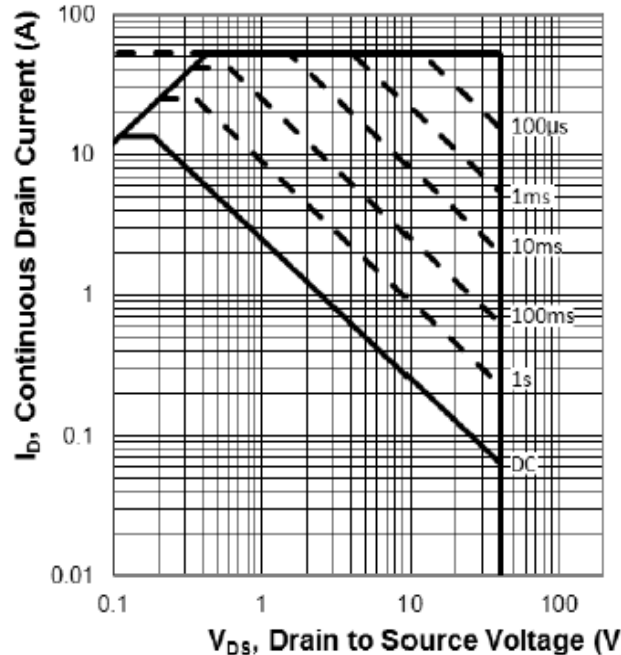


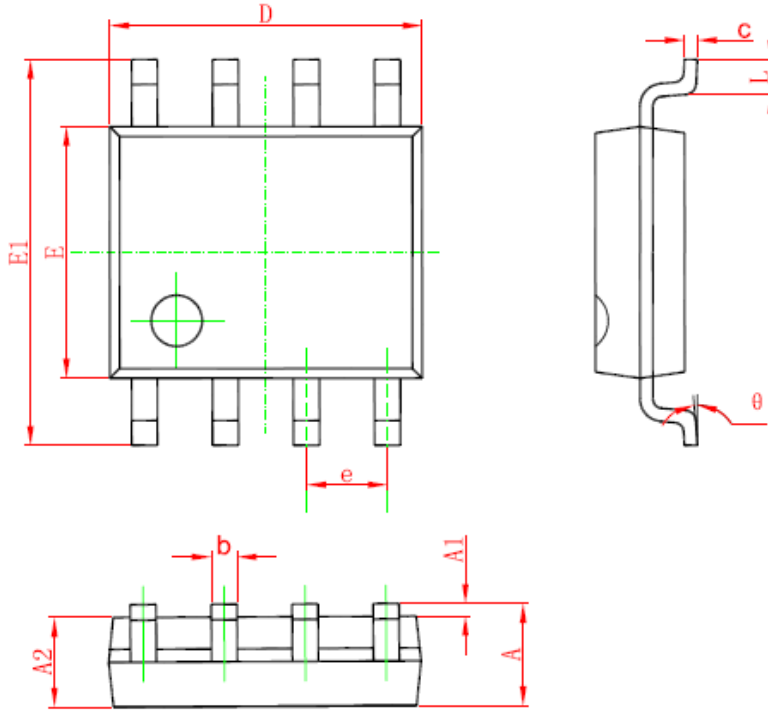
Figure 10: Maximum Safe Operation Area



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SOP- 8 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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